

# DIRECT BOND COPPER SUBSTRATES

## Specifications and Design Rules

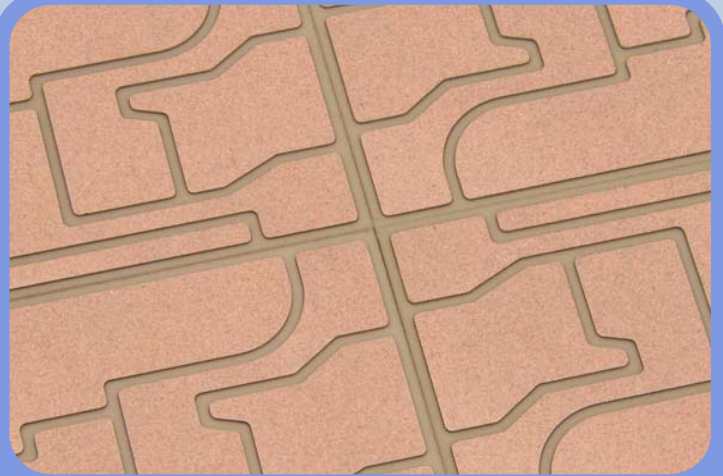
### Material Combinations

STANDARD Al <sub>2</sub> O <sub>3</sub>					
	Thickness	.010"	.015"	.025"	.040"
Copper	.005"	✓	✓	✓	✓
	.008"	✓	✓	✓	✓
	.012"		■	✓	✓

Al <sub>2</sub> O <sub>3</sub> OPTIONAL			
	Thickness	.030"	.035"
Copper	.005"		
	.008"	■	■
	.012"	■	■

■ Special order only.  
 .010" Copper is special order only.  
 Single side Copper available in limited configurations.

STANDARD AlN					
	Thickness	.010"	.015"	.025"	.040"
Copper	.005"		✓	✓	✓
	.008"		✓	✓	✓
	.012"			✓	✓



### Geometric Properties

Mastercard Overall Plate size: Nominal 5.5" x 7.5"  
 Actual 5.43" x 7.50"

Maximum usable Cu area: 5.0" x 7.0"

Overall thickness tolerance of ceramic + copper: +7%/-10%

Ceramic perimeter tolerance: Al<sub>2</sub>O<sub>3</sub> as fired ±2%  
 AlN as fired ±0.5%

Copper surface finish: R<sub>max</sub> ≤ .002"; R<sub>a</sub> ≤ .00008";  
 R<sub>z</sub> ≤ .00063"

### Physical Properties

Thermal conductivity: Al<sub>2</sub>O<sub>3</sub> 24-26 W/mK @ 20°C  
 AlN 170-180 W/mK @ 20°C

Electrical resistivity: >10<sup>14</sup> Ωcm

Dielectric constant: Al<sub>2</sub>O<sub>3</sub> 9.8 ±10% @ 1MHz  
 10.0 ±10% @ 1GHz  
 AlN 9.0 ±10% @ 1MHz

Dielectric loss: Al<sub>2</sub>O<sub>3</sub> 0.0003 @ 23°C, 1MHz  
 AlN 0.0005 @ 23°C, 1MHz

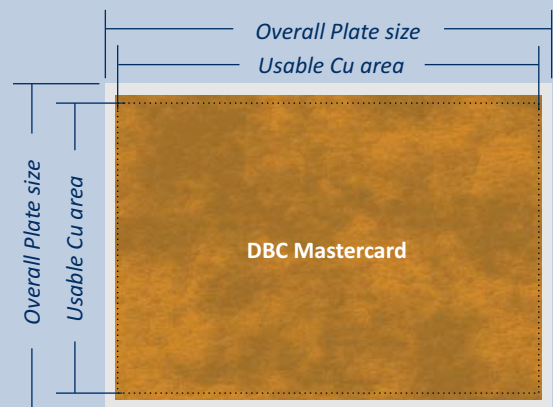
Dielectric strength (DC): Al<sub>2</sub>O<sub>3</sub> 20 kV/mm @ .025"  
 28 kV/mm @ .010"  
 AlN 20 kV/mm @ .025"

Copper peeling strength: Al<sub>2</sub>O<sub>3</sub> ≥22.8 lb/in. @ 2 in./min  
 (typical Cu-thickness .008")  
 AlN ≥28.6 lb/in. @ 2 in./min

Operating temperature: -55°C to +850°C  
 (critical in H<sub>2</sub> atmosphere >400°C)

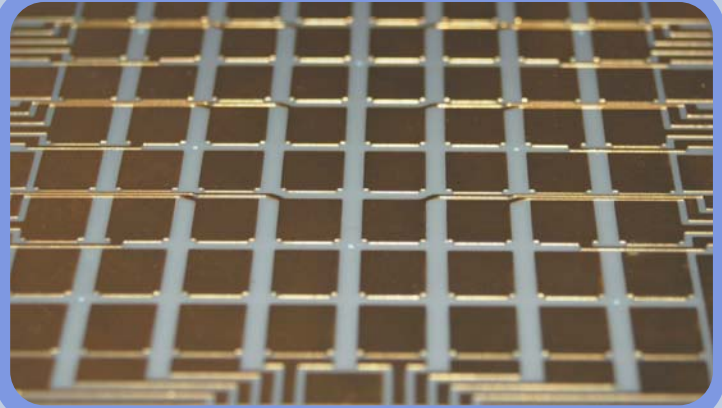
E-Module (blank ceramic): Al<sub>2</sub>O<sub>3</sub> 340 GPa  
 AlN 320 GPa

Electrical conductivity: 58 x 10<sup>6</sup> S/m  
 (Cu surface)



## Physical Properties Cont'd

Bending Strength:	$Al_2O_3 > 350 \text{ N/mm}^2$
<i>(blank ceramic)</i>	$AlN > 300 \text{ N/mm}^2$
	6.8 ppm/K @ 20°C - 300°C
Coefficient of linear thermal expansion for bare Cu:	$Al_2O_3$ 7.3 ppm/K @ 20°C - 600°C
<i>(dependent on Cu thickness)</i>	8.0 ppm/K @ 20°C - 1000°C
	4.7 ppm/K @ 20°C - 300°C
	$AlN$ 5.2 ppm/K @ 20°C - 600°C
	5.6 ppm/K @ 20°C - 1000°C



## Design Rules

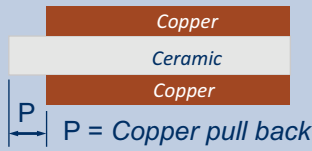
	Min. Width	Min. Space	Copper thickness	Minimum Pitch
Minimum width of Copper lines	Typical .012"		@ ≤ .005"	.024"
Minimum width of spaces	Minimum .010"		@ ≤ .005"	.020"
	Typical .020"		@ ≤ .008"	.040"
	Minimum .016"		@ ≤ .008"	.032"
	Typical .0275"		@ ≤ .010"	.056"
	Minimum .020"		@ ≤ .010"	.040"
	Typical .0275"		@ ≤ .012"	.056"
	Minimum .020"		@ ≤ .012"	.040"

Tighter tolerances are possible but not guaranteed in volume production.

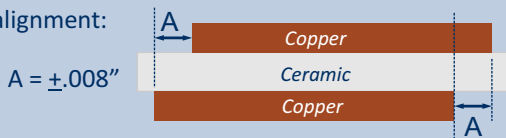
### Copper pull back:

*(lasered edge)*

typical  $P > .020" \pm .012"$   
 minimum  $P = .014" \pm .010"$   
*depends on copper thickness*

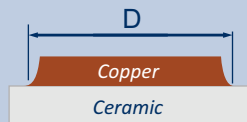


### Front to back alignment:



### Etching tolerance:

typical  $\pm .006"$  @  $\leq .008"$  Cu  
 minimum  $\pm .004"$  @  $\leq .008"$  Cu  
 typical  $\pm .008"$  @  $\leq .012"$  Cu  
 minimum  $\pm .006"$  @  $\leq .012"$  Cu

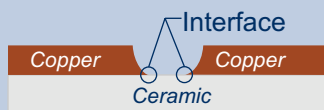


### Taper of etched pattern:

Maximum  $\frac{1}{2}$  Cu thickness



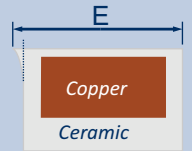
All Copper feature measurements are taken from ceramic and copper interface unless otherwise noted.



### Ceramic perimeter tolerance:

*single parts laser scribed*

$E = +.008"/-.002"$  @  $\leq .025"$   
 $E = +.012"/-.002"$  @  $> .025"$



### Chips along ceramic edge:

Length of chip: maximum 1 x ceramic thickness  
 Width of chip:  $\frac{1}{2}$  x ceramic thickness

### Surface plating (all over):

Electroless Nickel  $80\mu" - 400\mu"$  (8%±2% Phosphorus)  
 Pd  $2\mu" - 12\mu"$   
 Immersion Au  $0.4\mu" - 2\mu"$   
 Electroless Au  $2\mu" - 50\mu"$

### Bonding Area (wetting):

≥90%

Wire bonding: Standard Copper surface suitable for Stitch bond ≤8 mil Al, Au, Cu wire, > 8 mil wire requires a ball bond.

*no lift off allowed during pull test @ 10 mil Al wire*

